

**POLISHING PAD AND METHOD OF FABRICATING SEMICONDUCTOR
DEVICE USING THE SAME**

ABSTRACT OF THE DISCLOSURE

5 Provided is a polishing pad including a polishing layer, wherein the nuclear
magnetic resonance (NMR) ^{13}C spectrum of a processed composition prepared by adding
1 g of the polishing layer to a 0.3 M aqueous solution of potassium hydroxide (KOH) and
allowing the mixture to react in a closed container at a temperature of 150°C for 48 hours
includes a first peak appearing at 15 ppm to 18 ppm, a second peak appearing at 9 ppm to
10 11 ppm, a third peak appearing at 138 ppm to 143 ppm, and a fourth peak appearing at 55
ppm to 65 ppm, and the softening control index calculated by Equation 1 is 0.10 to 0.45.
The polishing pad includes the polishing layer having physical properties corresponding
to the softening control index, and thus may exhibit a removal rate and defect prevention
performance within desired ranges in polishing of a polishing target.

15 Fig. 1